NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1019-2** is Designed for VHF Communications up to 136 MHz

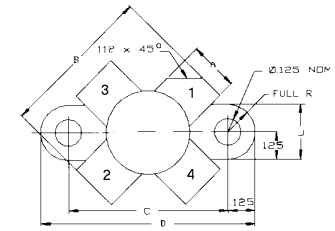
FEATURES:

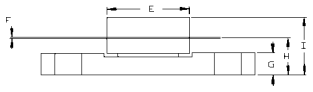
- P_G = 4.5 dB Minimum at 150 MHz
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	117 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.7 °C/W

PACKAGE STYLE .380 4 LEAD FLG





	MINIMUM	MAXIMUM
A	.220/5,59	.230/5,84
B	.785/19,94	
C	.778/19,29	.730/18,54
D	.970/24,64	.980/24,89
E		.305/7,74
F	.004/0,10	.006/0,15
G	.090/2,16	.105/2,67
H	.160/4,06	.180/4,57
I		.280/7,11
J	.240/6,10	.255/6,48

1 = COLLECTOR 3 & 4 = EMITTER 2 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA			65			V
BV_{CEO}	I_C = 200 mA			35			V
BV_{EBO}	I_E = 10 mA			4.0			V
I_{CBO}	V_{CB} = 30 V				1.5		mA
h_{FE}	V_{CE} = 5.0 V	I_C = 500 mA		5.0			---
C_{OB}	V_{CB} = 30 V		f = 1.0 MHz			150	pF
P_{OUT} P_G	V_{CC} = 13.5 V	P_{IN} = 10.6 W	f = 150 MHz	30 4.5			W dB